



TO-126 Bipolar Transistor D882



Specifications

TO-126 Bipolar Transistor D882

TO-126 Plastic-Encapsulate Transistors

D882 TRANSISTOR (NPN)

FEATURES

Power dissipation

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EB0}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	3	A
P _D	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

